

MRH135.12

Thyristor/Diode module

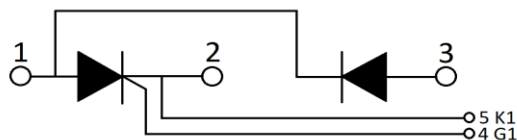
Features:

- International standard package
- High surge capability
- Glass passivated chip
- Simple mounting
- UL recognized, file no. E312789



Typical applications:

- Power converters
- Lighting control
- DC motor control and drives
- Heat and temperature control



Symbol	Characteristics	Test Conditions	Value			Unit
			Min	Typ	Max	
$V_{RSM/DSM}$	Non-repetitive reverse/forward blocking voltage	$T_j = 25^\circ\text{C}$			1300	V
$V_{RRM/DRM}$	Repetitive reverse/forward blocking voltage	$T_j = 25^\circ\text{C}$			1200	V
$I_T, I_{F(AV)}$	On-state/forward average current	180° half sine wave 50Hz $T_c = 84^\circ\text{C}$			135	A
$I_T, I_{F(RMS)}$	RMS on-state current	180° half sine wave 50Hz			210	A
I_{RRM} I_{DRM}	Repetitive peak current	at V_{DRM}/V_{RRM} $T_j = 125^\circ\text{C}$			25	mA
I_{TSM}, I_{FSM}	Surge non repetitive current	10ms half sine wave, $T_j = 25^\circ\text{C}$			3400	A
$I^2 t$	$I^2 t$ for fusing coordination	10ms half sine wave, $T_j = 25^\circ\text{C}$			57800	A ² s
V_{TO}	Threshold voltage	$T_j = 125^\circ\text{C}$			0.85	V
r_T	On-state slope resistance	$T_j = 125^\circ\text{C}$			2.10	mΩ
V_{TM}, V_{FM}	Peak on-state voltage	$T_j = 25^\circ\text{C}$; $I_T/I_F = 405\text{A}$			1.65	V
dv/dt	Critical rate of rise of off-state voltage	$V_D = 67\% V_{DRM}$, $T_j = 125^\circ\text{C}$, linear voltage rise			1000	V/μs
di/dt	Critical rate of rise of off-state current	$V_D = 1/2 V_{DRM}$, $T_j = 125^\circ\text{C}$, $I_G = 150\text{mA}$, $di_G/dt = 0.1 \text{ A/μs}$			150	A/μs
I_{GT}	Gate trigger current	$V_D = 6\text{V}$, $T_j = 25^\circ\text{C}$			150	mA
V_{GT}	Gate trigger voltage	$V_D = 6\text{V}$, $T_j = 25^\circ\text{C}$			3.0	V
V_{GD}	Gate non-trigger current	$V_D = 67\% V_{DRM}$, $T_j = 125^\circ\text{C}$			0.25	V
I_H	Holding current	$T_j = 25^\circ\text{C}$		150		mA
I_L	Latching current	$T_j = 25^\circ\text{C}$		200		mA
$R_{th(j-c)}$	Thermal resistance junction to case	Single side cooled per chip			0.18	°C/W
$R_{th(c-s)}$	Thermal resistance case to sink	Single side cooled per chip			0.10	°C/W
V_{ISO}	Isolation voltage	50Hz, RMS, $t = 1\text{min}$, $I_{ISO} : 1\text{mA (MAX)}$		3000		V
F_M	Mounting torque - copper plate (M6)		4		6	N·m
	Mounting torque - terminal (M6)		4		6	N·m
T_{stg}	Storage Temperature		-40		+125	°C
T_j	Operating Temperature		-40		+125	°C
W_t	Weight			180		g
Outline	M42					

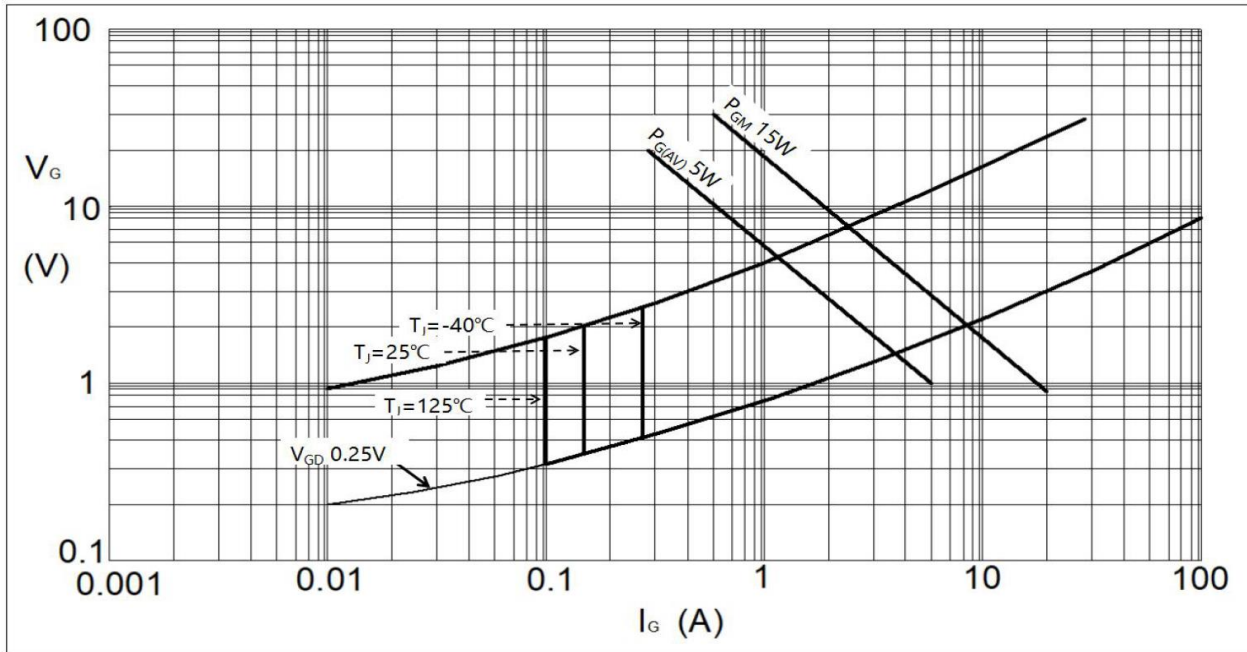


Fig1. Gate Trigger Characteristics

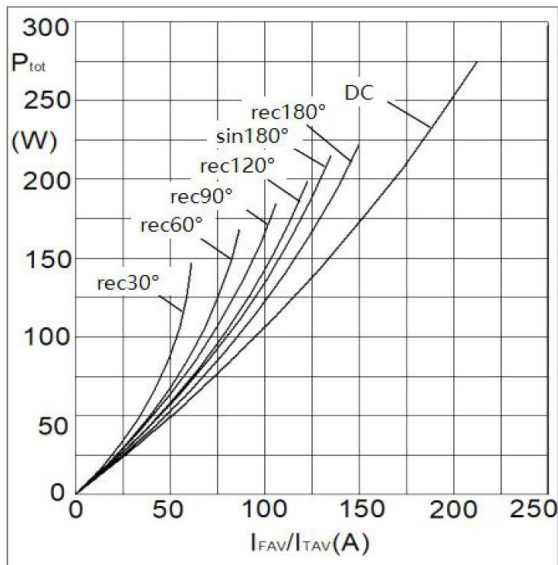


Fig2. Power Dissipation

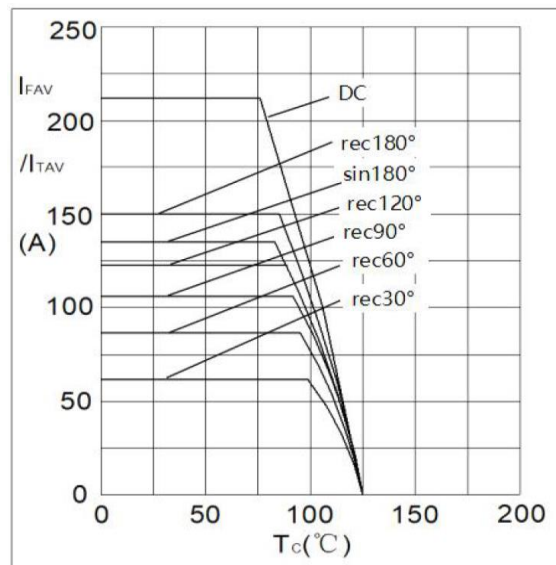


Fig3. Forward Current Derating Curve

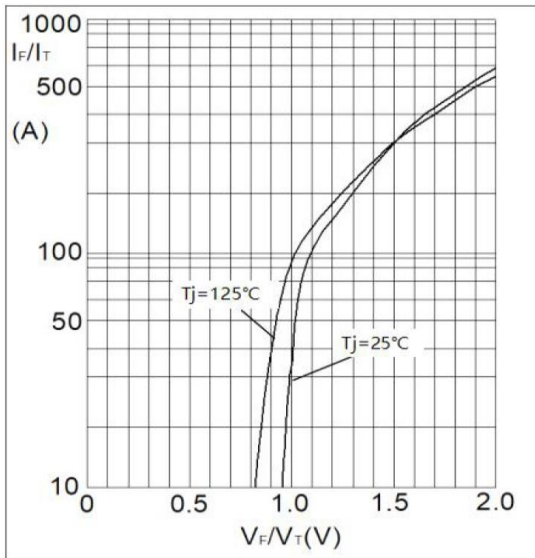


Fig4. Forward Characteristics

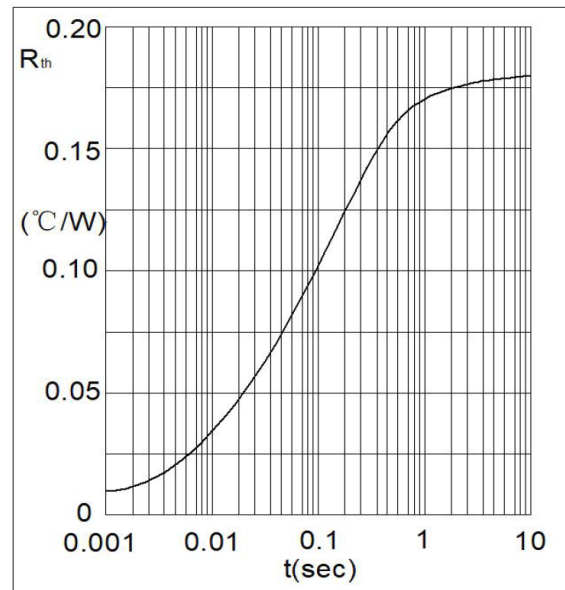


Fig5. Transient Thermal impedance

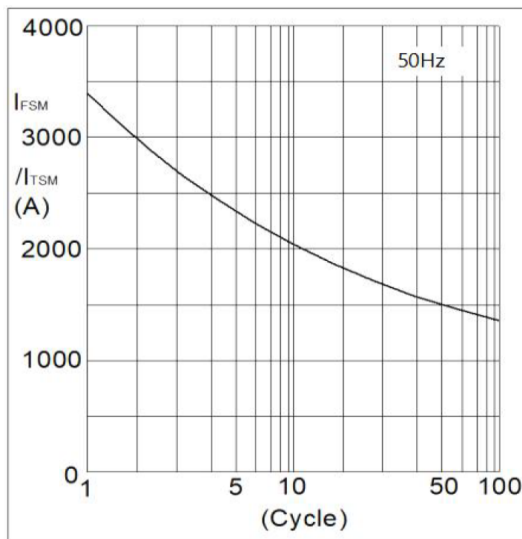
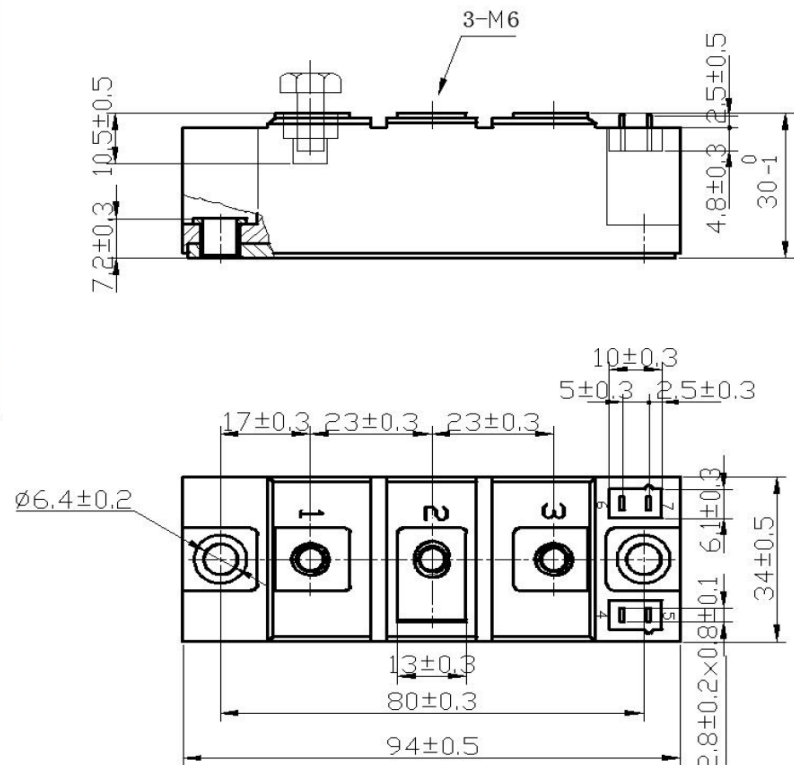


Fig6. Max Non-Repetitive Forward Surge Current



(dimensions in mm)

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